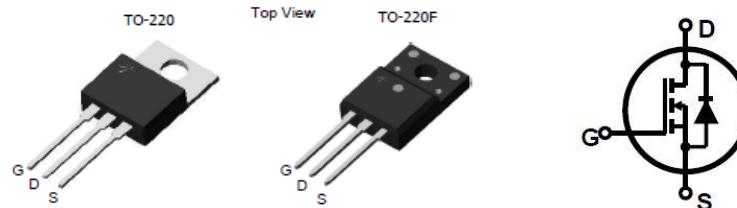


Features

- Low gate charge
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant
- Halogen free package
- JEDEC Qualification

N-channel MOSFET

BV_{DSS}	I_D	$R_{DS(on)}$
600V	16A	< 0.47Ω



Device	Package	Marking	Remark
TMP16N60A / TMPF16N60A	TO-220 / TO-220F	TMP16N60A / TMPF16N60A	RoHS
TMP16N60AG / TMPF16N60AG	TO-220 / TO-220F	TMP16N60AG / TMPF16N60AG	Halogen Free

Absolute Maximum Ratings

Parameter	Symbol	TMP16N60A(G)	TMPF16N60A(G)	Unit
Drain-Source Voltage	V_{DSS}	600		V
Gate-Source Voltage	V_{GS}	±30		V
Continuous Drain Current $T_C = 25\text{ °C}$	I_D	16	16 *	A
		9.97	9.97 *	A
Pulsed Drain Current (Note 1)	I_{DM}	64	64 *	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	194		mJ
Repetitive Avalanche Current (Note 1)	I_{AR}	16		A
Repetitive Avalanche Energy (Note 1)	E_{AR}	29		mJ
Power Dissipation $T_C = 25\text{ °C}$	P_D	290	48	W
		2.32	0.38	W/°C
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5		V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150		°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	T_L	300		°C

* Limited only by maximum junction temperature

Thermal Characteristics

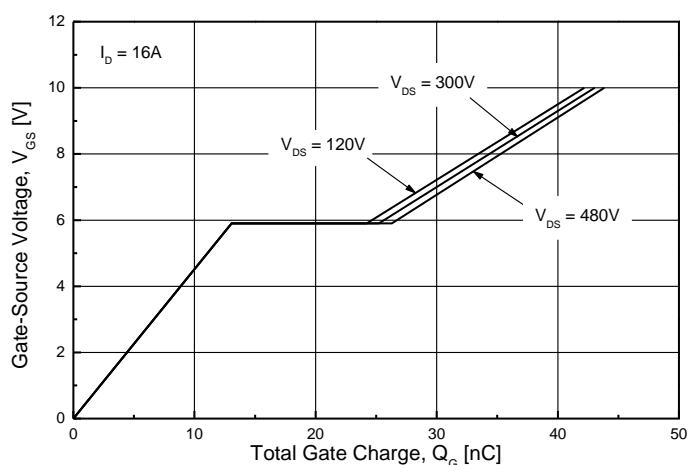
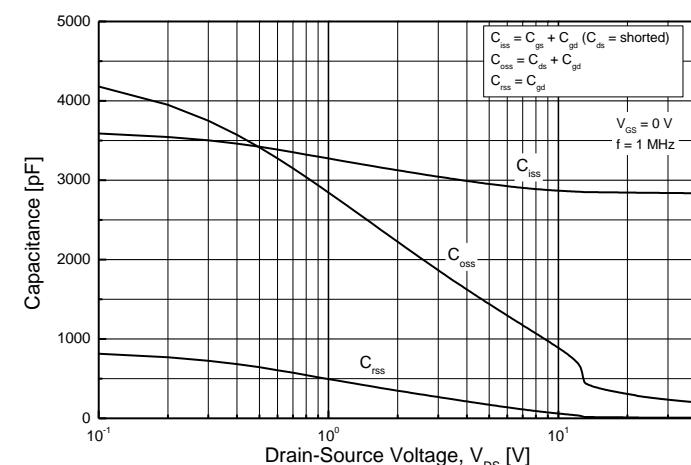
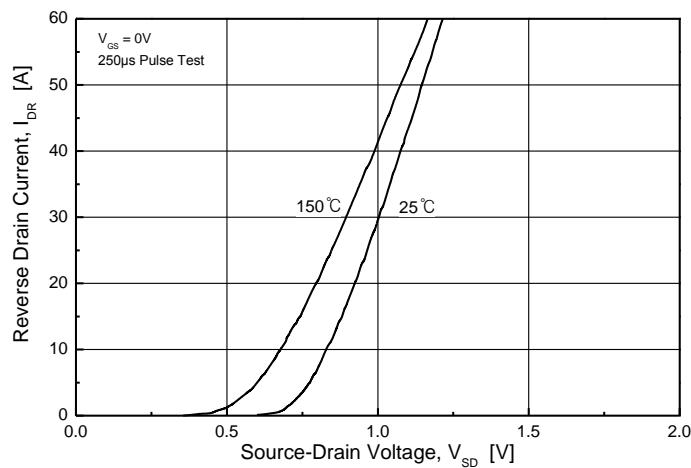
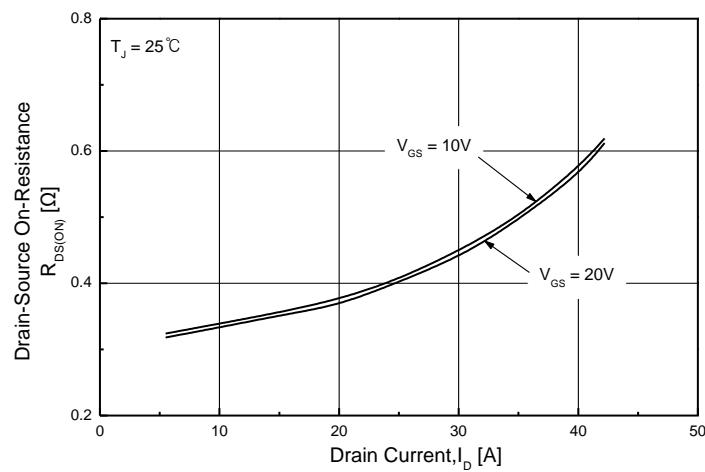
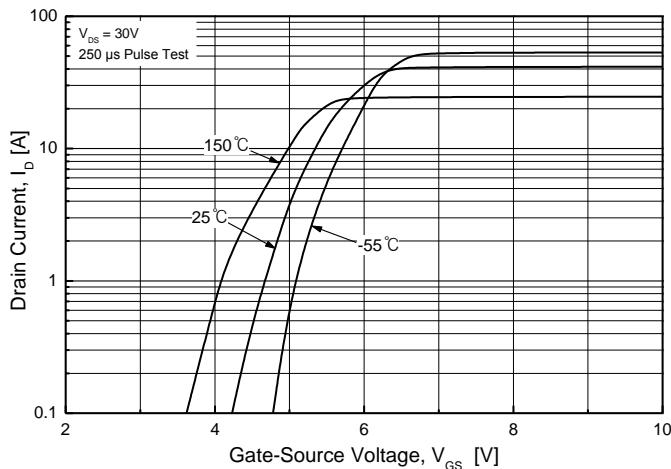
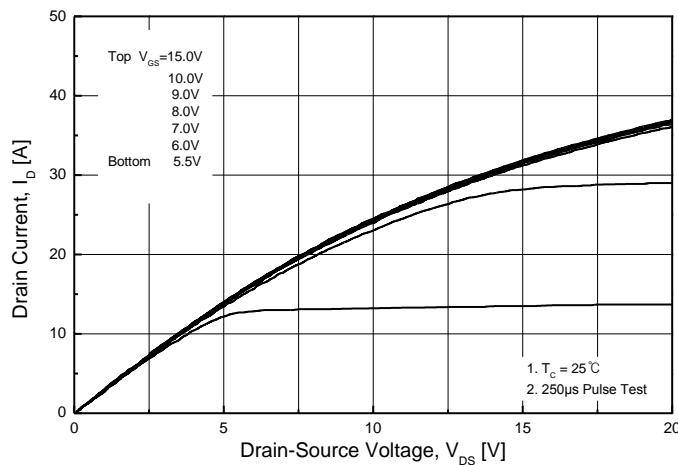
Parameter	Symbol	TMP16N60A(G)	TMPF16N60A(G)	Unit
Maximum Thermal resistance, Junction-to-Case	$R_{\theta JC}$	0.43	2.6	°C/W
Maximum Thermal resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	62.5	°C/W

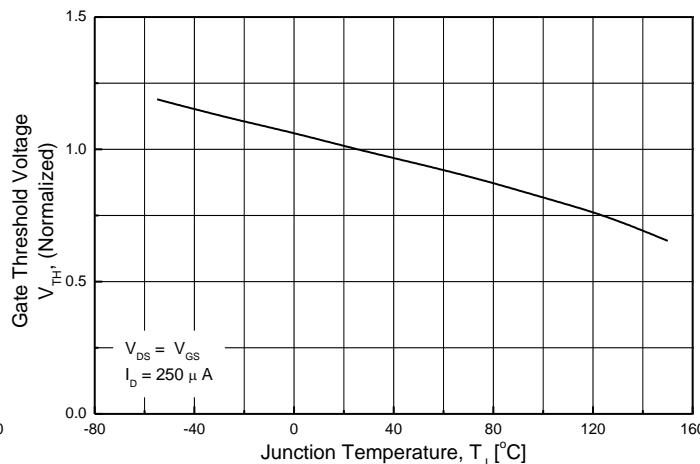
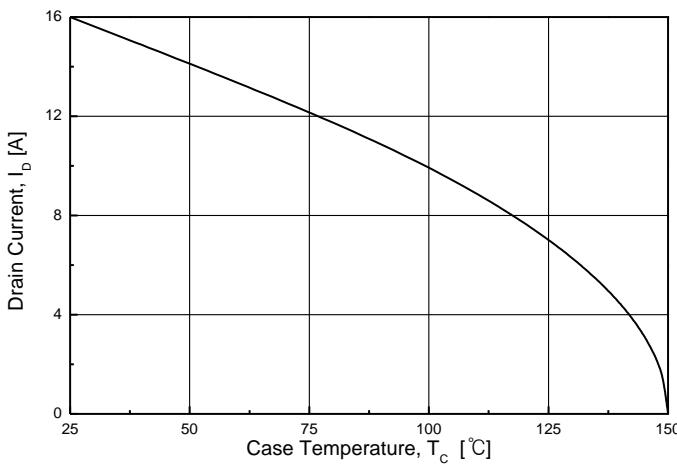
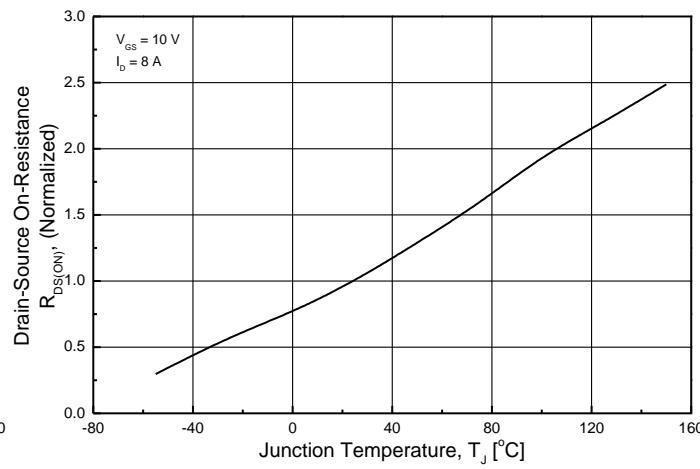
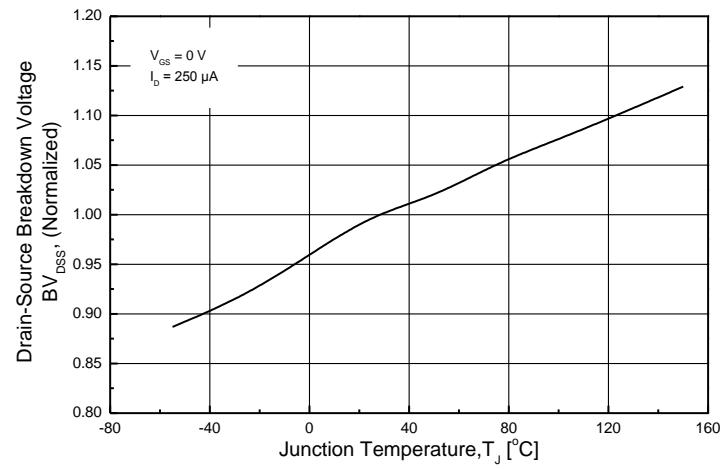
Electrical Characteristics : $T_c=25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test condition	Min	Typ	Max	Units
OFF						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}} = 0 \text{ V}, I_{\text{D}} = 250 \mu\text{A}$	600	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 600 \text{ V}, V_{\text{GS}} = 0 \text{ V}$	--	--	1	μA
		$V_{\text{DS}} = 480 \text{ V}, T_c = 125^\circ\text{C}$	--	--	10	μA
Forward Gate-Source Leakage Current	I_{GSSF}	$V_{\text{GS}} = 30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	--	--	100	nA
Reverse Gate-Source Leakage Current	I_{GSSR}	$V_{\text{GS}} = -30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	--	--	-100	nA
ON						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250 \mu\text{A}$	3	--	5	V
Drain-Source On-Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 10 \text{ V}, I_{\text{D}} = 8.0 \text{ A}$	--	0.38	0.47	Ω
Forward Transconductance ^(Note 4)	g_{FS}	$V_{\text{DS}} = 30 \text{ V}, I_{\text{D}} = 8.0 \text{ A}$	--	22	--	S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 25 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1.0 \text{ MHz}$	--	2840	--	pF
Output Capacitance	C_{oss}		--	262	--	pF
Reverse Transfer Capacitance	C_{rss}		--	10	--	pF
SWITCHING						
Turn-On Delay Time ^(Note 4,5)	$t_{\text{d(on)}}$	$V_{\text{DD}} = 300 \text{ V}, I_{\text{D}} = 16 \text{ A}, R_{\text{G}} = 25 \Omega, V_{\text{GS}} = 10 \text{ V}$	--	61	--	ns
Turn-On Rise Time ^(Note 4,5)	t_r		--	50	--	ns
Turn-Off Delay Time ^(Note 4,5)	$t_{\text{d(off)}}$		--	120	--	ns
Turn-Off Fall Time ^(Note 4,5)	t_f		--	34	--	ns
Total Gate Charge ^(Note 4,5)	Q_g	$V_{\text{DS}} = 480 \text{ V}, I_{\text{D}} = 16 \text{ A}, V_{\text{GS}} = 10 \text{ V}$	--	44	--	nC
Gate-Source Charge ^(Note 4,5)	Q_{gs}		--	13	--	nC
Gate-Drain Charge ^(Note 4,5)	Q_{gd}		--	14	--	nC
SOURCE DRAIN DIODE						
Maximum Continuous Drain-Source Diode Forward Current	I_s	----	--	--	16	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}	----	--	--	64	A
Drain-Source Diode Forward Voltage	V_{SD}	$V_{\text{GS}} = 0 \text{ V}, I_s = 16 \text{ A}$	--	--	1.5	V
Reverse Recovery Time ^(Note 4)	t_{rr}	$V_{\text{GS}} = 0 \text{ V}, I_s = 16 \text{ A}$	--	415	--	ns
Reverse Recovery Charge ^(Note 4)	Q_{rr}		$dI_F / dt = 100 \text{ A}/\mu\text{s}$	--	5.6	μC

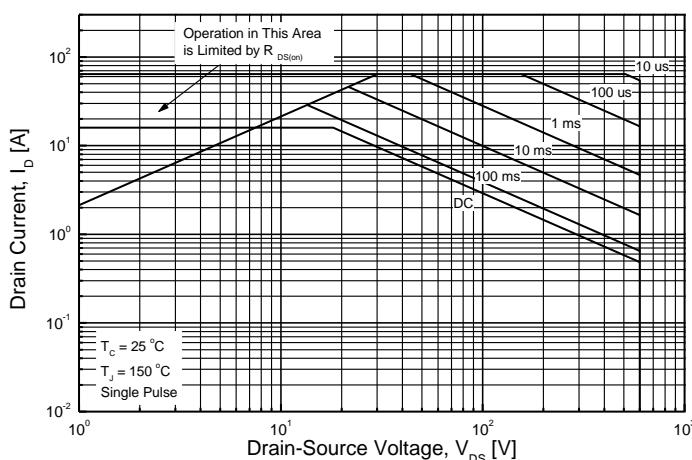
Note :

- Repeated rating : Pulse width limited by safe operating area
- $L=1.39\text{mH}, I_{\text{AS}} = 16\text{A}, V_{\text{DD}} = 50\text{V}, R_{\text{G}} = 25\Omega$, Starting $T_j = 25^\circ\text{C}$
- $I_{\text{SD}} \leq 16\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{\text{DD}} \leq BV_{\text{DS}}$, Starting $T_j = 25^\circ\text{C}$
- Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
- Essentially Independent of Operating Temperature Typical Characteristics

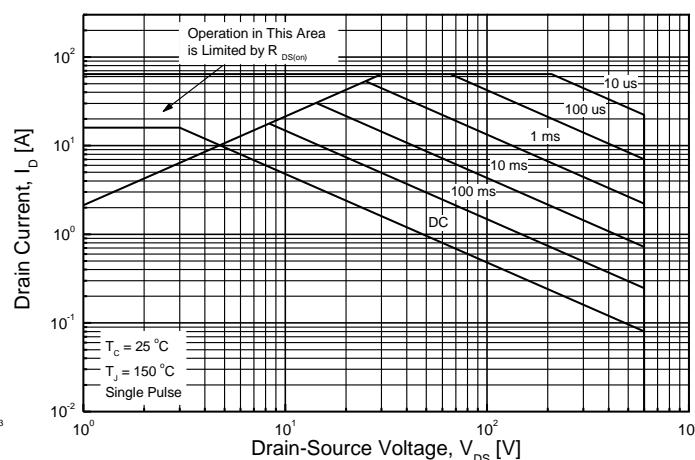


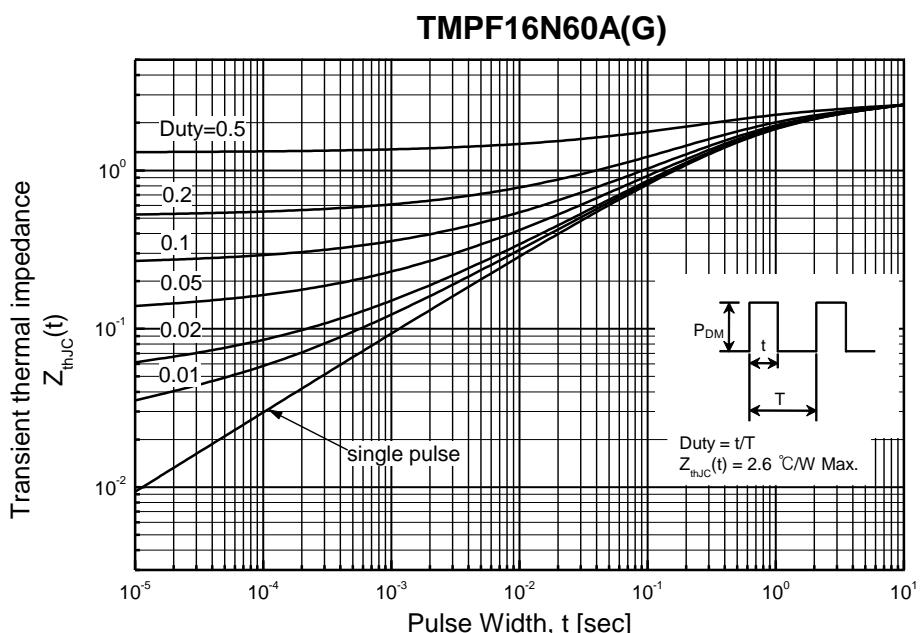
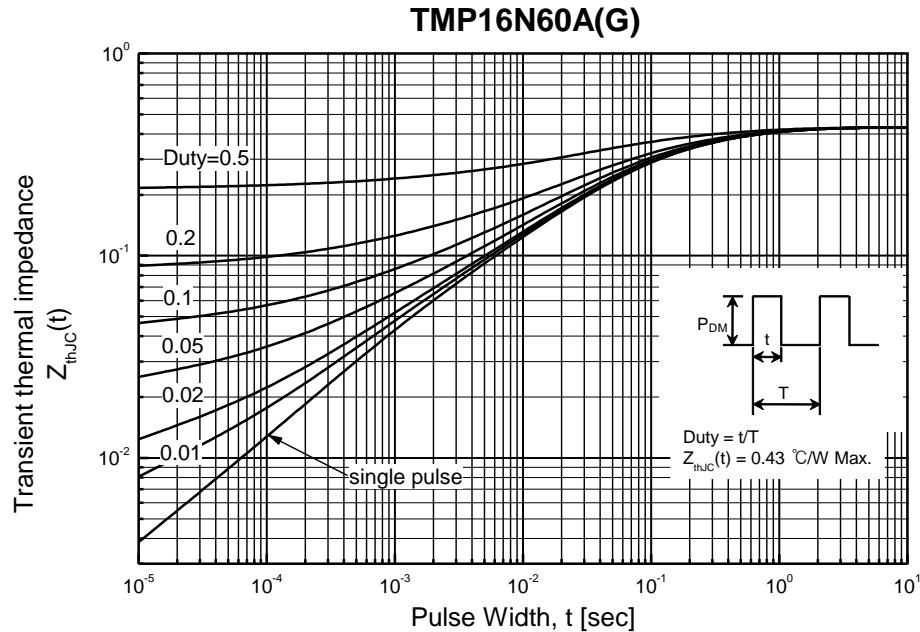


TMP16N60A(G)

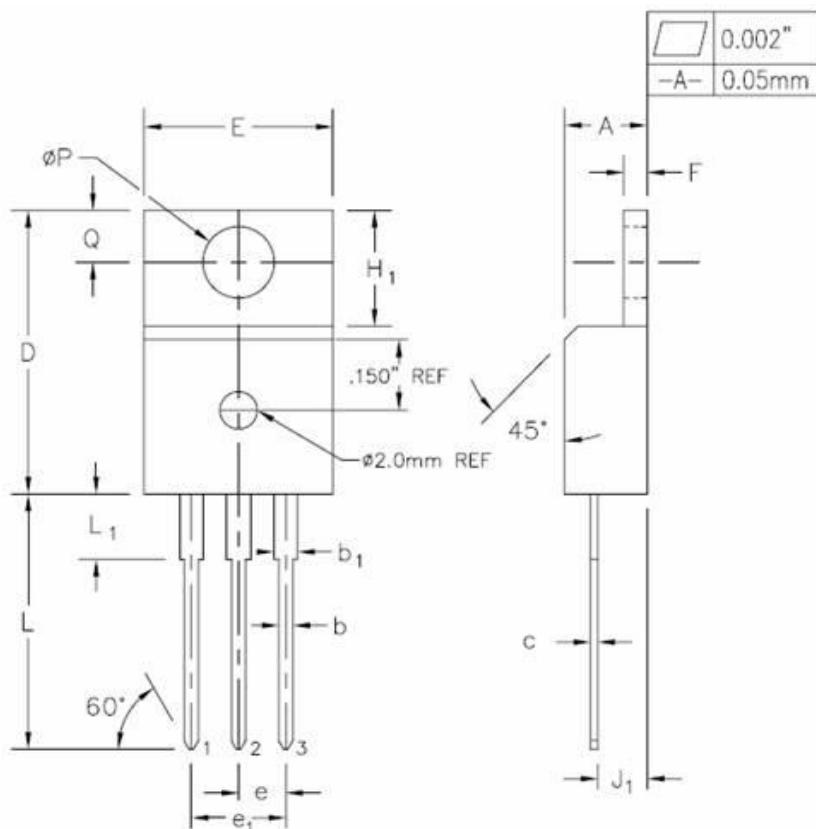


TMPF16N60A(G)



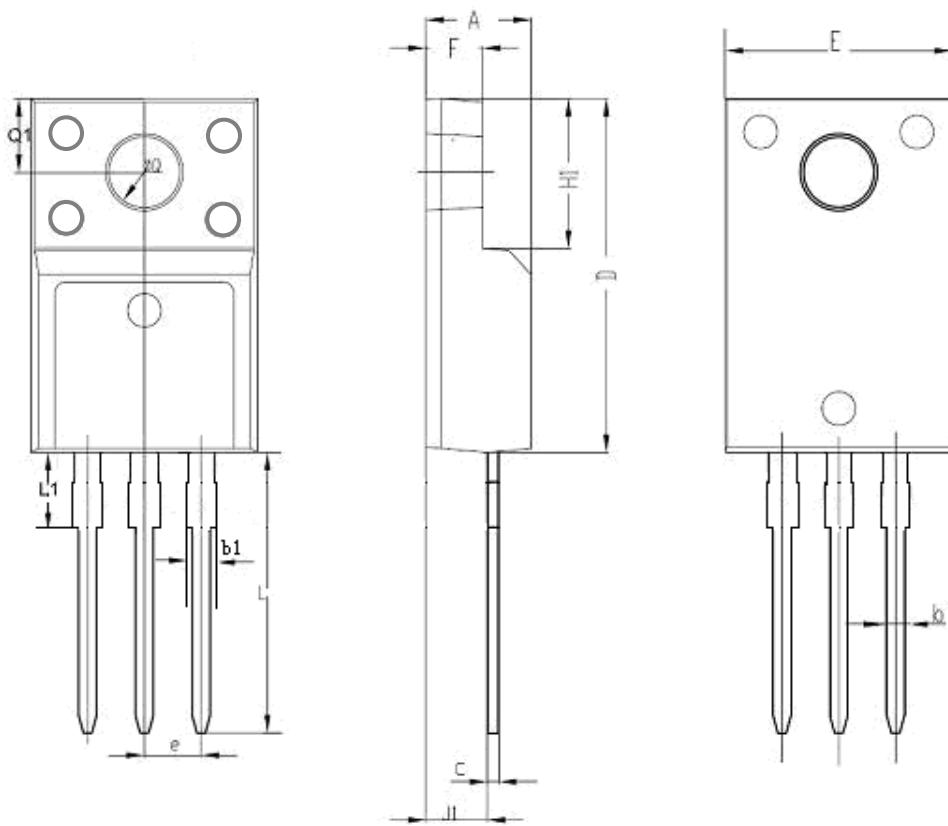


TO-220AB-3L MECHANICAL DATA



SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	0.170	0.180	4.32	4.57	
b	0.028	0.036	0.71	0.91	
b ₁	0.045	0.055	1.15	1.39	
c	0.014	0.021	0.36	0.53	
D	0.590	0.610	14.99	15.49	
E	0.395	0.410	10.04	10.41	
e	0.100	TYP.	2.54	TYP.	
e ₁	0.200	BSC	5.08	BSC	
F	0.048	0.054	1.22	1.37	
H ₁	0.235	0.255	5.97	6.47	
J ₁	0.100	0.110	2.54	2.79	
L	0.530	0.550	13.47	13.97	
L ₁	0.130	0.150	3.31	3.81	2
ØP	0.149	0.153	3.79	3.88	
Q	0.102	0.112	2.60	2.84	

TO-220F-3L MECHANICAL DATA



SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.178	0.194	4.53	4.93	
b	0.028	0.036	0.71	0.91	
C	0.018	0.024	0.45	0.60	
D	0.617	0.633	15.67	16.07	
E	0.392	0.408	9.96	10.36	
e	0.100 TYP.		2.54TYP.		
H1	0.256	0.272	6.50	6.90	
J1	0.101	0.117	2.56	2.96	
L	0.503	0.519	12.78	13.18	
ϕQ	0.117	0.133	2.98	3.38	
b1	0.045	0.055	1.15	1.39	
L1	0.114	0.130	2.9	3.3	
Q1	0.122	0.138	3.10	3.50	
F	0.092	0.108	2.34	2.74	